

BF 509

SILICON PLANAR PNP

VHF AGC AMPLIFIER

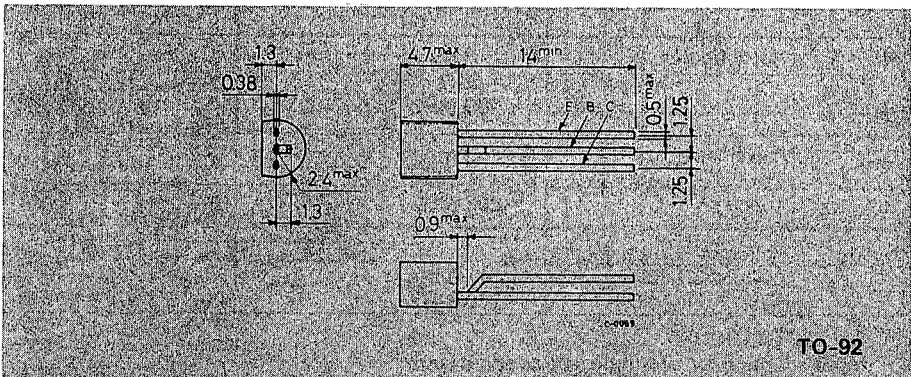
The BF 509 is a silicon planar epitaxial PNP transistor in Jedec TO-92 plastic package. It is intended for use as controlled VHF preamplifier when a high gain level with particularly reduced noise is required.

ABSOLUTE MAXIMUM RATINGS

V_{CBO}	Collector-base voltage ($I_E = 0$)	-40	V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)	-35	V
V_{EBO}	Emitter-base voltage ($I_C = 0$)	-4	V
I_C	Collector current	-30	mA
I_B	Base current	-5	mA
P_{tot}	Total power dissipation at $T_{amb} \leq 45^\circ\text{C}$	250	mW
T_{stg}	Storage temperature	-55 to 150	$^\circ\text{C}$
T_J	Junction temperature	150	$^\circ\text{C}$

MECHANICAL DATA

Dimensions in mm



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THERMAL DATA

$R_{thJ-amb}$	Thermal resistance junction-ambient	max	420 °C/W
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ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified)

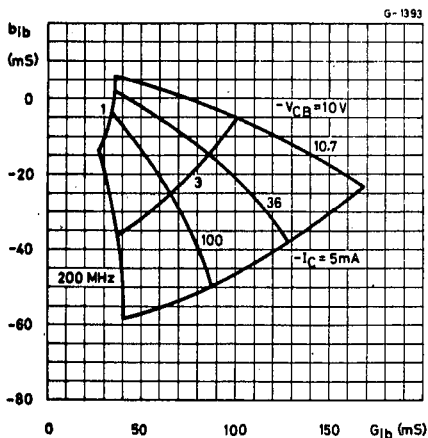
Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CBO} Collector cutoff current ($I_E = 0$)	$V_{CB} = -20\text{V}$			-200	nA
$V_{(BR)CEO}$ Collector-emitter breakdown voltage ($I_B = 0$)	$I_C = -5\text{ mA}$	-35			V
$V_{(BR)EBO}$ Emitter-base breakdown voltage ($I_C = 0$)	$I_E = -10\ \mu\text{A}$	-4			V
h_{FE} DC current gain	$I_C = -3\text{ mA}$ $V_{CE} = -10\text{V}$		70		—
f_T Transition frequency	$I_C = -3\text{ mA}$ $V_{CE} = -10\text{V}$ $f = 100\text{ MHz}$		700		MHz
C_{CBO} Collector-base capacitance	$I_E = 0$ $V_{CB} = -10\text{V}$ $f = 1\text{ MHz}$		0.8		pF
C_{rb} Reverse capacitance	$I_C = 0$ $V_{CB} = -10\text{V}$ $f = 1\text{ MHz}$		0.13		pF
NF**/** Noise figure	$I_C = -3\text{ mA}$ $V_{CC} = -10.8\text{V}$ $R_g = 50\ \Omega$ $f = 200\text{ MHz}$		1.5	2.5	dB
G_{pb}^* Power gain	$I_C = -3\text{ mA}$ $V_{CC} = -10.8\text{V}$ $R_L = 1\text{ k}\Omega$ $f = 200\text{ MHz}$		15	18	dB
$I_{C(AGC)}^*$ Collector current for $\Delta G_{pb} = 30\text{ dB}$	$V_{CC} = 10.8\text{V}$ $f = 200\text{ MHz}$	7.3		8.8	mA

* See TEST CIRCUIT

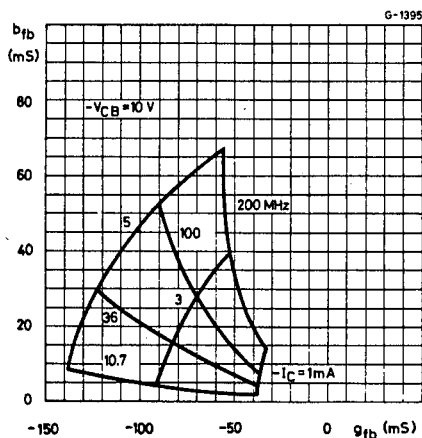
** Input adapting for optimum source admittance.

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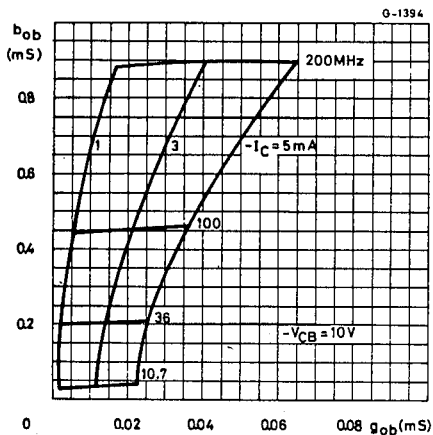
Typical input admittance



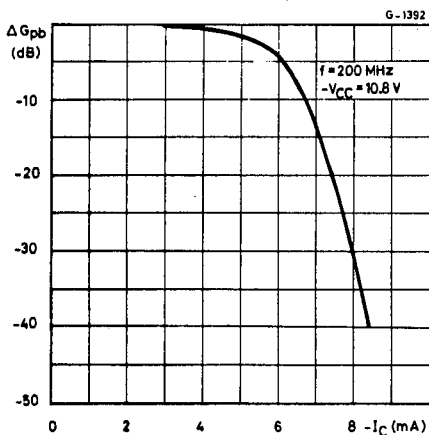
Typical transfer admittance



Typical output admittance



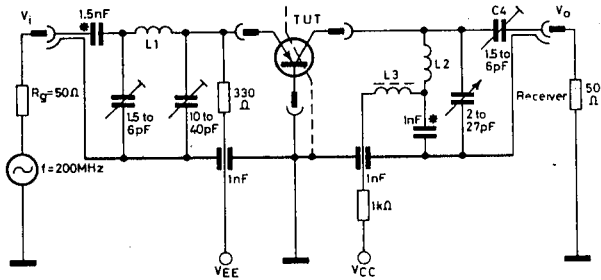
Typical power gain variation vs. AGC current



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TEST CIRCUIT

Power gain, AGC and noise figure



* Leadless ceramic disc capacitor
L1=3 turns 0.6mm enamel, 4mm dia.
L2=2 turns 1mm enamel, 6.5mm dia.

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